

IN THE CLAIMS:

1. (Currently Amended): A semiconductor device comprising:
a capacitor formed above a semiconductor substrate and including
~~a cylindrical-shaped storage electrode having a cylindrical projection, an edge of the cylindrical projection being located on an uppermost part of the cylindrical-shaped storage electrode,~~
~~a capacitor dielectric film formed on the storage electrode, and~~
~~a plate electrode formed on the capacitor dielectric film,~~
~~an upper cylinder edge of the storage electrode the edge of the cylindrical projection being~~
rounded and having a larger thickness than a thickness in ~~the a~~ rest portion. 1/2

2. (Currently Amended): A semiconductor device according to claim 1, wherein
~~the cylindrical-shaped storage electrode has a thickness gradually thickened toward to the upper cylinder edge the edge of the cylindrical projection.~~

3. (Currently Amended): A semiconductor device according to claim 1, wherein
~~a side surface of the storage electrode cylindrical projection is tilted and a peripheral circumferential length of a cylinder the cylindrical projection is gradually increased toward to the upper cylinder edge the edge of the cylindrical projection.~~

4. (Currently Amended): A semiconductor device according to claim 2, wherein
a side surface of the storage electrode cylindrical projection is tilted and a peripheral circumferential
length of a cylinder the cylindrical projection is gradually increased toward to the upper cylinder edge the
edge of the cylindrical projection.

b'
5-6. (Canceled)

7. (Currently Amended): A semiconductor device according to claim 1, wherein
an inner surface of the storage electrode at a border portion between a side surface and a bottom
surface of the cylindrical-shaped storage electrode is rounded.

8. (Currently Amended): A semiconductor device according to claim 2, wherein
an inner surface of the storage electrode at a border portion between a side surface and a bottom
surface of the cylindrical-shaped storage electrode is rounded.

9. (Currently Amended): A semiconductor device comprising:
a capacitor formed above a semiconductor substrate and including
a cylindrical-shaped storage electrode having a cylindrical projection, an edge of the
cylindrical projection being located on an uppermost part of the cylindrical-shaped storage electrode,

a capacitor dielectric film formed on the storage electrode, and
a plate electrode formed on the capacitor dielectric film,
the cylindrical-shaped storage electrode being formed of a metal film and having a larger
thickness at an upper cylinder edge the edge of the cylindrical projection than a thickness in a rest portion.
what's that?

10. (Currently Amended): A semiconductor device according to claim 9, wherein
the cylindrical-shaped storage electrode has a thickness gradually thickened toward the upper
cylinder edge the edge of the cylindrical projection.

11. (Currently Amended): A semiconductor device comprising:
a capacitor formed above a semiconductor substrate and including
a cylindrical-shaped storage electrode having a cylindrical projection, an edge of the
cylindrical projection being located on an uppermost part of the cylindrical-shaped storage electrode,
a capacitor dielectric film formed on the storage electrode, and
a plate electrode formed on the capacitor dielectric film,
the cylindrical-shaped storage electrode being formed of a metal film and an upper cylinder
edge of the storage electrode the edge of the cylindrical projection being rounded.

12. (Currently Amended): A semiconductor device according to claim 11, wherein
the cylindrical-shaped storage electrode has a thickness gradually thickened toward ~~to the upper~~
~~cylinder edge~~ the edge of the cylindrical projection.

B'

13-20. (Withdrawn)
